Silicon Carbide Schottky Diode

650 V, 20 A

Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 95 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- This Device is Pb-Free and is RoHS Compliant

Applications

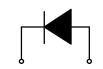
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



ON Semiconductor®

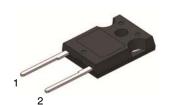
www.onsemi.com

V _{RRM}	I _F		
650 V	20 A		



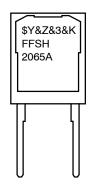
1. Cathode

2. Anode



TO-247-2LD CASE 340CL

MARKING DIAGRAM



\$Y = ON Semiconductor Logo &Z = Assembly Plant Code

&3 = Numeric Date Code &K = Lot Code

FFSH2065A = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSH2065A	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage	650	V		
E _{AS}	Single Pulse Avalanche Energy (Note 1)	95	mJ		
l _F	Continuous Rectified Forward Current	@ Tc < 146°C	20	Α	
		@ Tc < 135°C	25		
I _{F, Max}	Non-Repetitive Peak Forward Surge Current	Tc = 25°C, 10 μs	1100	Α	
		Tc = 150°C, 10 μs	1000	Α	
I _{F, SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	105	Α	
I _{F, RM}	Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	58	Α	
P _{tot}	Power Dissipation	Tc = 25°C	183	W	
		Tc = 150°C	31	W	
T _J , T _{STG}	, T _{STG} Operating and Storage Temperature Range		-55 to +175	°C	
	TO247 Mounting Torque, M3 Screw			Ncm	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. E_{AS} of 95 mJ is based on starting $T_J = 25^{\circ}C$, L = 0.5 mH, $I_{AS} = 19.5$ A, V = 50 V.

THERMAL CHARACTERISTICS

Symbol	Parameter	Rating	Unit
$R_{ hetaJC}$	Thermal Resistance, Junction to Case, Max.	0.82	°C/W

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH2065A	FFSH2065A	TO247-2L	Tube	N/A	N/A	30 Units

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_C = 25^{\circ}C \ unless \ otherwise \ noted)$

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V _F	Forward Voltage	IF = 20 A, Tc = 25°C	-	1.50	1.75	V
		IF = 20 A, Tc = 125°C	-	1.6	2.0	
		IF = 20 A, Tc = 175°C	-	1.72	2.4	
I _R	Reverse Current	VR = 650 V, Tc = 25°C	-	-	200	μΑ
		VR = 650 V, Tc = 125°C	-	-	400	
		VR = 650 V, Tc = 175°C	-	-	600	
Q _C	Total Capacitive Charge	V = 400 V	-	64	-	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	-	1085	-	pF
		V _R = 200 V, f = 100 kHz	-	117	-	
		VR = 400 V, f = 100 kHz	-	88	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

10-5

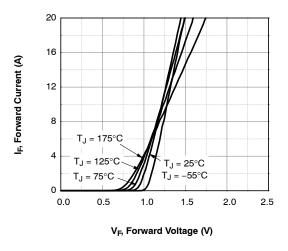


Figure 1. Forward Characteristics

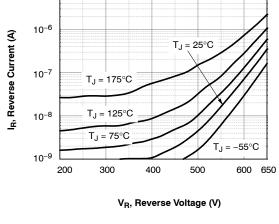


Figure 2. Reverse Characteristics

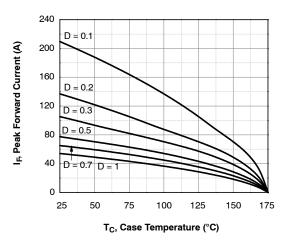


Figure 3. Current Derating

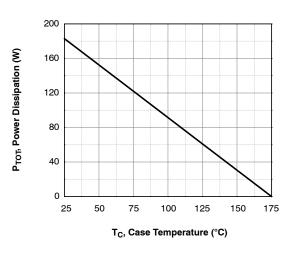


Figure 4. Power Derating

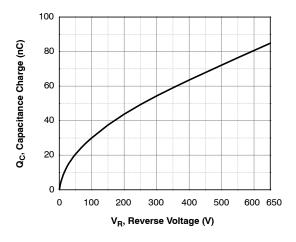


Figure 5. Capacitive Charge vs. Reverse Voltage

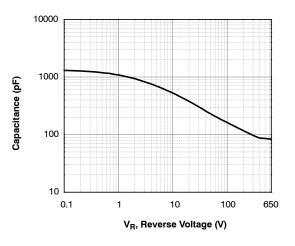


Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS (Continued)

 $(T_J = 25^{\circ}C \text{ unless otherwise noted})$

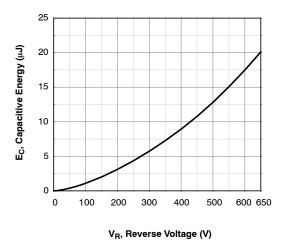


Figure 7. Capacitance Stored Energy

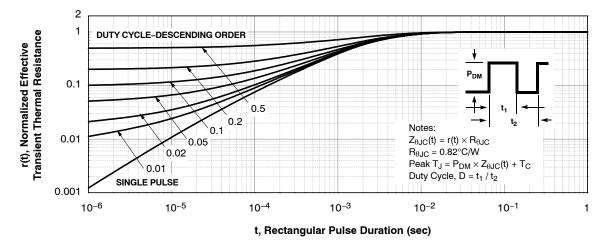
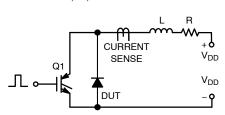


Figure 8. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

$$\label{eq:local_local_local} \begin{split} L &= 0.5 \text{ mH} \\ R &< 0.1 \ \Omega \\ V_{DD} &= 50 \ V \\ EAVL &= 1/2 LI2 \left[V_{R(AVL)} / (V_{R(AVL)} - V_{DD}) \right] \\ Q1 &= IGBT \left(BV_{CES} > DUT \ V_{R(AVL)} \right) \end{split}$$



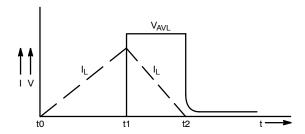
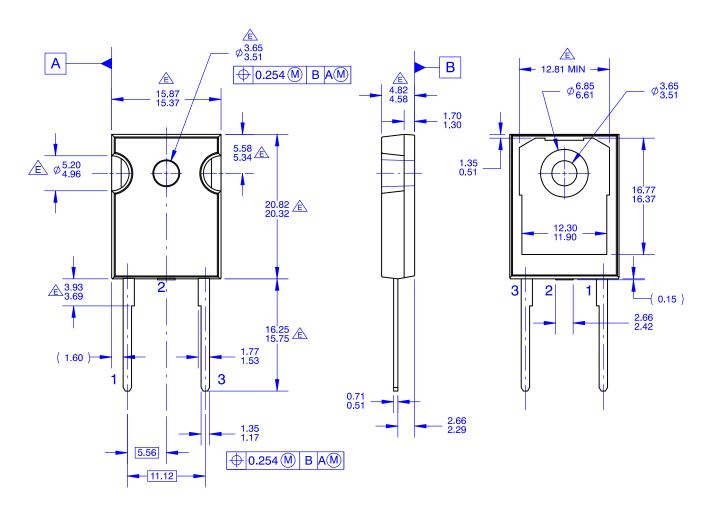


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

PACKAGE DIMENSIONS

TO-247-2LD CASE 340CL ISSUE O



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
 C. ALL DIMENSIONS ARE IN MILLIMETERS.
 D. DRAWING CONFORMS TO ASME Y14.5 2009.

- E DOES NOT COMPLY JEDEC STANDARD VALUE.

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns me rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor and wakes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor, "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices int

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada
Furope, Middle Fast and Africa Technical Support:

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910 Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative